

### Amendments to the Claims

The following listing of claims replaces all prior listings, and all prior versions, of claims in the application.

### Listing of Claims

1. (currently amended) A memory device comprising:  
a recording film including at least one element selected from the group consisting of Ge and Sb, ~~and~~ Te of 40 atom percent or more, and at least one element selected from the elements in a 2b group, a 1b group, 3a to 7a groups and an 8 group of 20 atom percent to 50 atom percent, said recording film being adapted to record ~~recording~~ information by causing a reversible phase change between a crystal phase and an amorphous phase; and  
an electrode for applying a voltage to said recording film.
2. (original) The memory device according to claim 1, wherein the element selected from said groups is Zn or Cd in the 2b group.
3. (original) The memory device according to claim 1, wherein a content of said at least one element selected from the group consisting of Ge and Sb is less than 40 atom percent.
4. (original) The memory device according to claim 1, wherein a content of said at least one element selected from the group consisting of Ge and Sb is 25 atom percent to 35 atom percent.
5. (currently amended) The memory device according to claim 1, wherein said device is ~~used~~ adapted to be operable in an atmosphere at 140°C or more.

6. (currently amended) The memory device according to claim 1, comprising ~~it has an area adjacent to an element region between said recording film and an electrode in which a content of Zn or Cd is relatively more than by 10 atom percent or more in content.~~

7. (currently amended) The memory device according to claim 1, wherein said memory element has a multilayer structure with electrodes for voltage application and is adapted to transmit 30 percent or more of transmits a recording light or reproducing reproduction light which is applied to it by 30 percent or more.

8. (currently amended) A memory device comprising:  
a plurality of memory cells;  
a plurality of word lines for selecting said plurality of memory cells;  
a plurality of data lines placed to be orthogonal to said plurality of word lines and having signals read thereto from said plurality of memory cells, and  
each of said plurality of memory cells comprising a recording film including at least one element selected from the group consisting of Ge and Sb, ~~and~~ Te of 40 atom percent or more, and at least one element selected from the elements in a 2b group, a 1b group, 3a to 7a groups and an 8 group of 20 atom percent to 50 atom percent, said recording film being adapted to record ~~recording~~ information by causing a reversible phase change between a crystal phase and an amorphous phase, and an electrode for applying a voltage to said recording film.

9. (original) The memory device according to claim 8, wherein an insulating film is provided between said recording film and said electrode.

10. (original) The memory device according to claim 4, wherein both of the Ge and Sb are included and the ratio between Ge and Sb is in the range of 1:2 to 2:1.